

SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET **FSS273**— General-Purpose Switching Device **Applications**

Features

- Motor drive applications.
- · Inverter drive applications.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		45	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱ _D		8	А
Drain Current (PW≤10s)	١D	Duty cycle≤1%	8.5	А
Drain Current (PW≤10µs)	IDP	Duty cycle≤1%	32	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm ² X0.8mm), PW≤10s	2.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			11-2
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	45			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =45V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =8A	6	10		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=8A, VGS=10V		16	22	mΩ
	R _{DS} (on)2	ID=4A, VGS=4V		24	34	mΩ
Input Capacitance	Ciss	VDS=20V, f=1MHz		2225		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		260		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		190		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		27		ns
Rise Time	tr	See specified Test Circuit.		55		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		150		ns
Fall Time	tf	See specified Test Circuit.		80		ns

Marking : S273

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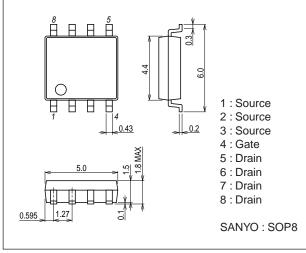
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Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	
Total Gate Charge	Qg	V _{DS} =24V, V _{GS} =10V, I _D =8A		40		nC
Gate-to-Source Charge	Qgs	VDS=24V, VGS=10V, ID=8A		6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =24V, V _{GS} =10V, I _D =8A		8		nC
Diode Forward Voltage	VSD	IS=8A, VGS=0V		0.82	1.2	V

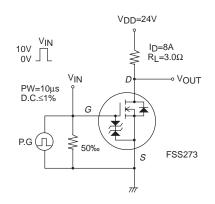
Package Dimensions

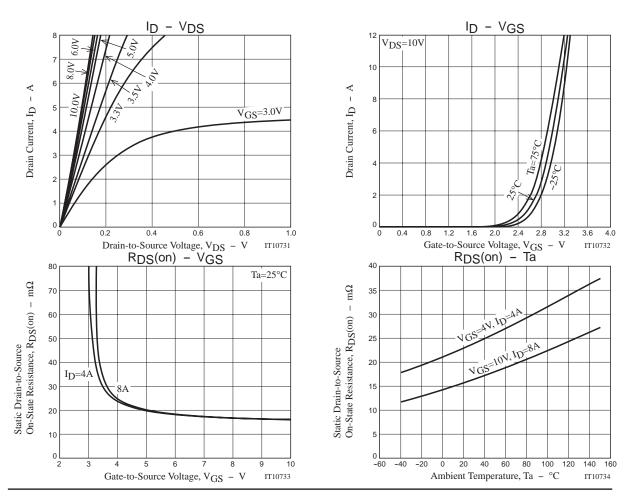
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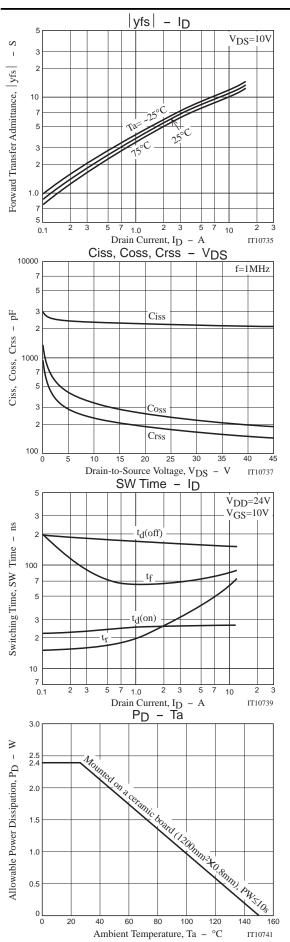
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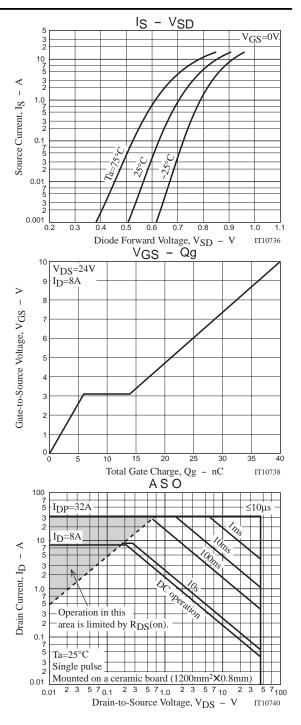


Switching Time Test Circuit









Note on usage : Since the FSS273 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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